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| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99) | Application Number | 10550853 |
| | Filing Date | 2005-09-22 |
| | First Named Inventor | MEUNIER-BEILLARD, PHILIPPE |
| | Art Unit | 2823 |
| | Examiner Name | NGUYEN, KHIEM D |
| | Attorney Docket Number | NL03 0357 US1 |

U.S.PATENTS

| Examiner Initial* | Cite No | Patent Number | Kind Code ¹ | Issue Date | Name of Patentee or Applicant of cited Document | Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear |
|-------------------|---------|---------------|------------------------|------------|---|--|
| /KN/ | 1 | 5378651 | A | 1995-01-03 | AGNELLO, PAUL D.; ET AL | |
| /KN/ | 2 | 6251188 | B1 | 2001-06-26 | HASHIMOTO, TSUYOSHI; ET AL | |

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U.S.PATENT APPLICATION PUBLICATIONS

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|-------------------|---------|--------------------|------------------------|------------------|---|--|
| /KN/ | 1 | 20030003646 | A1 | 2003-01-02 | WIEBE BARTELD DE BOER | |

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FOREIGN PATENT DOCUMENTS

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|-------------------|---------|--------------------------------------|-----------------------------|------------------------|------------------|---|--|--------------------------|
| /KN/ | 1 | 0459122 | EP | A2 | 1991-12-04 | INTERNATIONAL BUSINESS MACHINES CORPORATION | | <input type="checkbox"/> |

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NON-PATENT LITERATURE DOCUMENTS

/Khiem Nguyen/

04/12/2009

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| | |
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| Attorney Docket Number | NL03 0357 US1 |

| Examiner Initials* | Cite No | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published. | T ⁵ |
|--------------------|---------|--|--------------------------|
| /KN/ | 1 | AGNELLO, P.D., ET AL: "HEAVY ARSENIC DOPING OF SILICON GROWN BY ATMOSPHERIC-PRESSURE CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURES"; APPL. PHYS. LETT. 60 (4); JANUARY 27, 1992; PAGES 454 - 456 | <input type="checkbox"/> |
| | 2 | AGNELLO, P.D., ET AL: "SILICON EPITAXY FROM SILANE BY ATMOSPHERIC-PRESSURE CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURES"; APPL. PHYS. LETT. 61 (11); SEPTEMBER 14, 1992; PAGES 1298 - 1300 | <input type="checkbox"/> |
| | 3 | YANG, MIN, ET AL: "PHOSPHORUS DOPING AND SHARP PROFILES IN SILICON AND SILICON-GERMANIUM EPITAXY BY RAPID THERMAL CHEMICAL VAPOR DEPOSITION"; JOURNAL OF THE ELECTROCHEMICAL SOCIETY, 147 (9); PAGES 3541 - 3545; JUNE 2, 2000 | <input type="checkbox"/> |
| | 4 | SEDGWICK, T.O., ET AL: "HIGH PHOSPHORUS DOPING OF EPITAXIAL SILICON AT LOW TEMPERATURE AND ATMOSPHERIC PRESSURE"; APPL. PHYS. LETTER. 58 (17); APRIL 29, 1991; PAGES 1896 - 1898 | <input type="checkbox"/> |
| ↓ /KN/ | 5 | ALONSO, J.C., ET AL: "LOW-TEMPERATURE EPITAXIAL GROWTH OF UNDOPED AND N-DOPED SILICON BY PHOTOCHEMICAL VAPOR USING DEPOSITION SiH ₄ /SiH ₂ Cl ₂ /H ₂ /PH ₃ MIXTURES"; ELSVIER SEQUOIA S.A. LAUSANEE, CH, VOL 327, NO. 1/2, 1994; PAGES 98-104 | <input type="checkbox"/> |

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| Examiner Signature | /Khiem Nguyen/ | Date Considered | 04/12/2009 |
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